

Method Of Forming Silicon-Containing Insulation Film Having Low Dielectric Constant and Low Film Stress

Abstract of the Disclosure

[0068] A silicon-containing insulation film is formed on a substrate by plasma polymerization by introducing a reaction gas comprising (i) a source gas comprising a silicon-containing hydrocarbon compound containing at least one vinyl group (Si-vinyl compound), and (ii) an additive gas, into a reaction chamber where a substrate is placed; and applying radio-frequency power to the gas to cause plasma polymerization, thereby depositing an insulation film on the substrate.

H:\DOCS\KOA\ASMP137.APP.DOC
081903